Updated Search 762582 11 December 2003 DB L Number Hits Search Text (US-6309524-\$ or US-5932077-\$ or US-5522975-\$ USPAT: 2003/12/11 10:53 US-PGPUB; or US-6197181-\$ or US-5415890-\$ or US-5849171-\$ EPO: JPO: or US-4163705-\$ or US-5433840-\$ or US-4430173-\$ or US-6294059-\$ or US-5437777-\$ **DERWENT** or US-4666735-\$ or US-6140234-\$ or US-6117784-\$ or US-4749449-\$ or US-4490220-\$ or US-4303443-\$ or US-6458251-\$ or US-6143155-\$ or US-5462670-\$ or US-5230782-\$ or US-4956097-\$ or US-4299671-\$ or US-3833486-\$).did. or (US-20020000372-\$ or US-20020008034-\$ or US-20020005359-\$).did. or (US-5342806-\$ or GB-2285174-\$).did. or (JP-05311496-\$ or JP-07193214-\$ or JP-56158424-\$ or JP-56161221-\$ or JP-03146698-\$ or JP-63026400-\$).did. or (GB-2285174-\$ or JP-56158424-\$ or JP-63026400-\$ or GB-1222969-\$).did. 2003/12/11 6080291.pn. USPAT; 5 09:42 US-PGPUB; EPO; JPO; DERWENT USPAT; 2003/12/11 10:33 6 0 762582.apn. US-PGPUB; EPO; JPO; DERWENT 2003/12/11 10:57 ((US-6309524-\$ or US-5932077-\$ or USPAT: 7 US-5522975-\$ or US-6197181-\$ or US-5415890-\$ US-PGPUB; EPO: JPO: or US-5849171-\$ or US-4163705-\$ or DERWENT US-5433840-\$ or US-4430173-\$ or US-6294059-\$ or US-5437777-\$ or US-4666735-\$ or US-6140234-\$ or US-6117784-\$ or US-4749449-\$ or US-4490220-\$ or US-4303443-\$ or US-6458251-\$ or US-6143155-\$ or US-5462670-\$ or US-5230782-\$ or US-4956097-\$ or US-4299671-\$ or US-3833486-\$).did. or (US-20020000372-\$ or US-20020008034-\$ or US-20020005359-\$).did. or (US-5342806-\$ or GB-2285174-\$).did. or (JP-05311496-\$ or JP-07193214-\$ or JP-56158424-\$ or JP-56161221-\$ or JP-03146698-\$ or JP-63026400-\$).did. or (GB-2285174-\$ or JP-56158424-\$ or JP-63026400-\$ or GB-1222969-\$).did.) and (activat\$) 2003/12/11 10:57 108 205/183.ccls. and (activat\$ or palladium) USPAT: 8 US-PGPUB: EPO; JPO; DERWENT 9 57 (205/183.ccls. and (activat\$ or palladium)) and USPAT: 2003/12/11 11:06 electroless US-PGPUB; EPO; JPO; DERWENT

	T		T	
10	207	205/\$.ccls. and (electroless same ((palladium or pd!)	USPAT;	2003/12/11 11:08
		with (tin or Sn!)))	U5-PGPUB;	
			EPO; JPO;	
			DERWENT	
11	98	205/\$.ccls. and (electroless same activat\$7 same	USPAT;	2003/12/11 11:16
[((palladium or pd!) with (tin or Sn!)))	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
12	1	205/\$.ccls. and (electroless same activat\$7 same	USPAT;	2003/12/11 11:25
		((palladium or pd!) same (tin or Sn!)) same	US-PGPUB;	
	1	(semiconductor or microelectronic))	EPO; JPO;	
			DERWENT	
13	80	204/\$.ccls. and ((semiconductor or microelectronic)	USPAT;	2003/12/11 11:28
		and (shield\$3 adj plate))	US-PGPUB;	
		, , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
}			DERWENT	
14	5	(204/\$.ccls. and ((semiconductor or microelectronic)	USPAT;	2003/12/11 11:26
		and (shield\$3 adj plate))) and (electroplat\$6)	US-PGPUB;	
		(a.v. a. a. 4 a. m. 6 k.m. a.	EPO; JPO;	
	i		DERWENT	
15	0	204/\$.ccls. and ((semiconductor or microelectronic)	USPAT;	2003/12/11 11:28
		and (thie\$3 adj plate))	US-PGPUB;	2005/12/11 11:20
		and (mode day plate))	EPO; JPO;	
			DERWENT	
16	0	204/\$.ccls. and ((semiconductor or microelectronic)	USPAT;	2003/12/11 11:29
		and (thie\$5 adj plate))	US-PGPUB;	2003/12/11 11.29
ļ		and (mode day plane))	EPO; JPO;	
			DERWENT	
17	6	204/\$.ccls. and ((semiconductor or microelectronic)	USPAT;	2003/12/11 11:54
•		and (thie\$5 adj electrode))	US-PGPUB;	2003/12/11 11:54
			EPO; JPO;	
			DERWENT	
18	128	204/\$.ccls. and ((semiconductor or microelectronic)	USPAT;	2003/12/11 11:55
••	120	and ((clean\$6 or rins\$6) with (spin\$6 or spun)))	US-PGPUB;	2003/12/11 11:55
		and ((clean to of this to) with (spin to of spun)))	EPO; JPO;	
19	107	204/\$.ccls. and ((semiconductor or microelectronic)	DERWENT	2002/12/11/11/57
19	10/		USPAT;	2003/12/11 11:56
		and ((clean\$6 or rins\$6) with (spin\$6 or spun) with (dry\$5 or dried)))	US-PGPUB;	
		(drypo or dried)))	EPO; JPO;	
20	63	201/\$ pale and //gamiaand/cata	DERWENT	2002/42/44 57
20	65	204/\$.ccls. and ((semiconductor or microelectronic)	USPAT;	2003/12/11 11:57
		and ((clean\$6 or rins\$6) with (spin\$6 or spun) with	US-PGPUB;	
		(dry\$5 or dried))) and electroplat\$5	EPO; JPO;	
		7/2502	DERWENT	
] -	0	762582.apn.	USPAT;	2003/12/11 10:33
			US-PGPUB;	
			EPO; JPO;	
		////E44/ 400II) ///O74/ 4/0II) ///O0000000000000000000000000000000000	DERWENT	
-	9	(("5116430") or ("3716462") or ("3930963")).PN.	USPAT;	2003/04/29
			US-PGPUB;	13:53
			EPO; JPO;	
			DERWENT	

<u></u>	1 4	Transport to t	11-5.7	T = = = = = = = = = = = = = = = = = = =
-	1	jp-51149131-\$.did.	USPAT;	2003/04/29
			US-PGPUB;	12:13
			EPO; JPO;	
			DERWENT	
-	2	4163705.pn.	USPAT;	2003/04/29
			US-PGPUB;	12:13
			EPO; JPO;	
			DERWENT	
_	7	(("5849171") or ("4430173") or ("5433840")).PN.	USPAT;	2003/04/30
			US-PGPUB;	09:43
İ			EPO; JPO;	05.10
			DERWENT	
	2657	204/198,212,232,242,273,275.1.ccls.	1	2002/04/20
_	2037	2047190,212,232,242,273,273.1.ccis.	USPAT;	2003/04/29
			US-PGPUB;	13:55
			EPO; JPO;	
			DERWENT	
-	773	204/224r.ccls.	USPAT;	2003/04/29
			US-PGPUB;	13:55
			EPO; JPO;	
			DERWENT	
-	3270	204/198,212,232,242,273,275.1.ccls. 204/224r.ccls.	USPAT;	2003/04/29
			US-PGPUB;	13:55
			EPO; JPO;	
			DERWENT	
-	35	(204/198,212,232,242,273,275.1.ccls.	USPAT;	2003/04/29
		204/224r.ccls.) and electroless and (electrolytic or	US-PGPUB;	14:04
		electroplating) and robot	EPO; JPO;	
		, 3,	DERWENT	
_	58753	204/\$.ccls.	USPAT;	2003/04/29
İ			US-PGPUB;	14:04
			EPO; JPO;	- \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
			DERWENT	
-	55	204/\$.ccls. and electroless and (electrolytic or	USPAT;	2003/04/29
		electroplating) and robot	US-PGPUB;	14:04
		ciberropia/mg/ana ropor	EPO; JPO;	17.07
			1	
	20	(201/\$ and and alcohology and (-1+1-+	DERWENT	2002/04/20
-	20	(204/\$.ccls. and electroless and (electrolytic or	USPAT;	2003/04/29
		electroplating) and robot) not	US-PGPUB;	14:14
		((204/198,212,232,242,273,275.1.ccls.	EPO; JPO;	
		204/224r.ccls.) and electroless and (electrolytic or	DERWENT	
		electroplating) and robot)	110047	0000101
-	2	6080291.pn.	USPAT;	2003/04/29
			US-PGPUB;	14:07
			EPO; JPO;	
		00444	DERWENT	
-	813	204/\$.ccls. and (robot or robotic)	USPAT;	2003/04/29
			US-PGPUB;	14:14
			EPO; JPO;	
			DERWENT	
-	78	(204/\$.ccls. and (robot or robotic)) and electroless	USPAT;	2003/04/29
			US-PGPUB;	14:15
			EPO; JPO;	
			DERWENT	

Г			- 	
_	81	204/\$.ccls. and electroless and (robot or robotic or	USPAT;	2003/04/29
		(transfer adj unit) or (transfer adj device) or	US-PGPUB;	14:16
		(transfer adj arm))	EPO; JPO;	
			DERWENT	
-	26	(204/\$.ccls. and electroless and (robot or robotic or	USPAT;	2003/04/29
		(transfer adj unit) or (transfer adj device) or	US-PGPUB;	14:17
		(transfer adj arm))) not (204/\$.ccls. and electroless	EPO; JPO;	
		and (electrolytic or electroplating) and robot) not	DERWENT	
		((204/\$.ccls. and electroless and (electrolytic or		
		electroplating) and robot) not		
		((204/198,212,232,242,273,275.1.ccls.		
		204/224r.ccls.) and electroless and (electrolytic or		
		electroplating) and robot))		
-	26	(204/\$.ccls. and electroless and (robot or robotic or	USPAT;	2003/04/29
		(transfer adj unit) or (transfer adj device) or	US-PGPUB;	14:33
		(transfer adj arm))) not (204/\$.ccls. and electroless	EPO; JPO;	
		and (electrolytic or electroplating) and robot) not	DERWENT	
		((204/198,212,232,242,273,275.1.ccls.		
		204/224r.ccls.) and electroless and (electrolytic or		
		electroplating) and robot)		
-	2	6197181.pn.	USPAT;	2003/04/29
			US-PGPUB;	14:21
			EPO; JPO;	
			DERWENT	
-	2	jp-56158424-\$.did.	USPAT;	2003/04/29
			US-PGPUB;	14:34
			EPO; JPO;	
			DERWENT	
-	1	1982-04830E.NRAN.	DERWENT	2003/04/29
				14:33
-	2	jp-05311496-\$.did.	USPAT;	2003/04/29
			US-PGPUB;	14:35
			EPO; JPO;	
			DERWENT	
-	2	jp-07193214-\$.did.	USPAT;	2003/04/29
			US-PGPUB;	14:37
]		EPO; JPO;	
	4	1005 217002 ND AN	DERWENT	0000104100
-	1	1995-217803.NRAN.	DERWENT	2003/04/29
	2	: 02000241 & J:J	LICDAT	14:37
1	6	jp-02000341-\$.did.	USPAT;	2003/04/29
1	,		US-PGPUB;	14:39
1			EPO; JPO;	
	1	1990 047945 ND 4N	DERWENT	2002/04/20
_	1	1990-047945.NRAN.	DERWENT	2003/04/29
_	2	jp-56161221-\$.did.	I LEDAT	14:39
-		Jp-sototeet-p.uid.	USPAT;	2003/04/29
	i		US-PGPUB;	14:42
			EPO; JPO;	
	1	jp-51149131-\$.did.	DERWENT	2002/04/20
-	1	Jρ-511 -1 3151-φ.αια.	USPAT;	2003/04/29
			US-PGPUB;	14:43
			EPO; JPO;	
<u></u>			DERWENT	

	1	1074 75402V ND 4N1	DERWENT	2003/04/20
-	1	1976-75692X.NRAN.	DERWENT	2003/04/29 14:42
	2	: 02144408 & did	USPAT;	2003/04/29
-	-	jp-03146698-\$.did.	US-PGPUB;	14:44
			EPO; JPO;	17.77
			DERWENT	
	2	:- 0E008E00 & 4:1	USPAT;	2003/05/01 10:11
_	-	jp-05098500-\$.did.	US-PGPUB;	2003/05/01 10:11
			EPO; JPO;	
			DERWENT	
	2	jp-62235499-\$.did.	USPAT;	2003/04/29
_		Jp-02235499-\$.did.	US-PGPUB:	14:46
			EPO; JPO;	14.40
			DERWENT	
_	2	jp-63026400-\$.did.	USPAT;	2003/04/29
_		Jp-63026400-\$.ala.	US-PGPUB;	14:50
			EPO; JPO;	14.50
			DERWENT	
	1	1997wo-??22733.ap,prai.	USPAT;	2003/04/29
-	1	1997 W0-??227 33.αβ,βrαι.	US-PGPUB;	14:51
			EPO; JPO;	14.51
			DERWENT	
	0	 wo-22733-\$.did.	USPAT;	2003/04/29
-	"	wo-22/33-φ.did.	US-PGPUB;	14:52
			EPO; JPO;	14.52
			DERWENT	
	0	wo-00022733-\$.did.	USPAT;	2003/04/29
-	"	W0-000227 33-φ.αια.	US-PGPUB;	14:52
			EPO; JPO;	14.52
			DERWENT	
	0	wo-97022733-\$.did.	USPAT:	2003/04/29
		wo γγομμγού φ.αια.	US-PGPUB;	14:52
			EPO; JPO;	11.32
			DERWENT	
_	58753	204/\$.ccls.	USPAT;	2003/04/29
	55,55	20 17 \$1.0015.	US-PGPUB;	15:10
			EPO; JPO;	
			DERWENT	
-	708	204/\$.ccls. and (electroless and (electrolytic or	USPAT;	2003/04/29
		electroplating or electroplate))	US-PGPUB;	15:11
			EPO; JPO;	
			DERWENT	1
-	82	(204/\$.ccls. and (electroless and (electrolytic or	USPAT;	2003/04/29
		electroplating or electroplate))) and (robot or robotic	US-PGPUB;	15:12
		or ((transfer or conveyance or conveyor) adj (means!	EPO; JPO;	
		or unit or device or system or arm)))	DERWENT	
-	160054	205/\$.ccls. or 427/\$.ccls.	USPAT;	2003/04/29
			US-PGPUB;	15:47
			EPO; JPO;	
			DERWENT	
-	14963	(205/\$.ccls. or 427/\$.ccls.) and (semiconductor or	USPAT;	2003/04/29
[wafer)	US-PGPUB;	15:48
			EPO; JPO;	
<u> </u>			DERWENT	

			1-11-11	
-	759	((205/\$.ccls. or 427/\$.ccls.) and (semiconductor or	USPAT;	2003/04/29
		wafer)) and electroless and (electroplating or	US-PGPUB;	15:49
1		electroplated or electroplate or electrolytic or	EPO; JPO;	
		electrochemically)	DERWENT	
-	54	((205/\$.ccls. or 427/\$.ccls.) and (semiconductor or	USPAT;	2003/04/29
		wafer)) and (electroless near2 (tank or bath)) and	US-PGPUB;	15:49
		((electroplating or electroplated or electroplate or	EPO; JPO;	
		electrolytic or electrochemically) near2 (tank or	DERWENT	
		bath))		
-	60	((205/\$.ccls. or 427/\$.ccls.) and (semiconductor or	USPAT;	2003/04/29
		wafer)) and (electroless near2 (tank or bath or	US-PGPUB;	15:54
		chamber)) and ((electroplating or electroplated or	EPO; JPO;	
		electroplate or electrolytic or electrochemically)	DERWENT	
		near2 (tank or bath or chamber))		
-	7	(((205/\$.ccls. or 427/\$.ccls.) and (semiconductor or	USPAT;	2003/04/29
		wafer)) and (electroless near2 (tank or bath or	US-PGPUB;	15:51
		chamber)) and ((electroplating or electroplated or	EPO; JPO;	
		electroplate or electrolytic or electrochemically)	DERWENT	
		near2 (tank or bath or chamber))) and (robot or		
	}	robotic or ((transfer or conveyor or conveyance) near		
		(arm or unit or device or means!)))		
-	29	(((205/\$.ccls. or 427/\$.ccls.) and (semiconductor or	USPAT;	2003/04/29
		wafer)) and (electroless near2 (tank or bath or	US-PGPUB;	15:55
		chamber)) and ((electroplating or electroplated or	EPO; JPO;	
		electroplate or electrolytic or electrochemically)	DERWENT	
		near2 (tank or bath or chamber))) and ((copper adj		
		sulfate) or "Cuso.sub.4")		
-	8	(("5500315") or ("5310580") or ("5389496") or	USPAT;	2003/04/30
		("5139818")).PN.	US-PGPUB;	08:52
			EPO; JPO;	
			DERWENT	
-	0	electroless and ((copper adj sulfate) or "cuso.sub.4")	USPAT;	2003/04/30
		and ((chlorine or chloride) adj ions) and (sufuric adj	US-PGPUB;	08:54
		acid)	EPO; JPO;	
	1896	alpotentage and ((company add sulfate) and (1999)	DERWENT	2002/04/20
-	0,000	electroless and ((copper adj sulfate) or "cuso.sub.4")	USPAT;	2003/04/30
			US-PGPUB;	08:54
			EPO; JPO;	
	1019	(electroless and ((copper adj sulfate) or	DERWENT USPAT;	2003/04/30
] -	1019	"cuso.sub.4")) and (sulfuric adj acid)	USPAT; US-PGPUB;	08:54
		caso.sub.+)) and (surraine day acid)	EPO; JPO;	00.54
			DERWENT	
_	220	((electroless and ((copper adj sulfate) or	USPAT;	2003/04/30
		"cuso.sub.4")) and (sulfuric adj acid)) and	US-PGPUB;	08:55
		(((polyethylene or polypropylene) adj glycol) or pegl or	EPO; JPO;	
		ppg!)	DERWENT	
-	52	(((electroless and ((copper adj sulfate) or	USPAT;	2003/04/30
		"cuso.sub.4")) and (sulfuric adj acid)) and	US-PGPUB;	08:55
		(((polyethylene or polypropylene) adj glycol) or pegl or	EPO; JPO;	
		ppg!)) and sulfur and nitrogen	DERWENT	

"cuso sub 4")) and (sulfuric adj acid)) and ((((phyethyknea or polypropylene) adj glycol) or pegl or pegl) or p					
((po/pethylene an polypropylene) add glycol) or pegl or ppgl) and sulfur and nitrogen) and (chlorine or chloride) 0	_	51	((((electroless and ((copper adj sulfate) or	USPAT;	2003/04/30
psp() and sulfur and nitragen) and (chlorine or chloride) uk-1222969-\$.did. USPAT; US			"cuso.sub.4")) and (sulfuric adj acid)) and	US-PGPUB;	09:06
chloride) uk-122969-\$.did. USPAT: USPAPUB: EPO. JPO: DERWENT USPAT: USPAPUB: EPO. JPO: DERWENT USPAT: USPAPUB: EPO. JPO: DERWENT USPAT: USPAPUB: EPO. JPO: DERWENT USPAT: USPAPUB: EPO. JPO: DERWENT USPAT: USPAPUB: EPO. JPO: DERWENT USPAT: USPAPUB: EPO: JPO: DERWENT USPAT: USPAPUB: EPO: JPO: DERWENT USPAT: USPAPUB: EPO: JPO: DERWENT USPAT: USPAPUB: EPO: JPO: DERWENT USPAT: USPAT: USPAPUB: EPO: JPO: DERWENT USPAT: USPEPUB: EPO: JPO: DERWENT USPAT: USPEPUB: EPO: JPO: DERWENT USPAT: USPAT: USPAT: USPAT: USPAT: USPEPUB: EPO: JPO: DERWENT USPAT: US			(((polyethylene or polypropylene) adj glycol) or peg! or	EPO; JPO;	
-			ppg!)) and sulfur and nitrogen) and (chlorine or	DERWENT	
1 gb-1222969-\$.did.			chloride)		
1 gb-1222969-\$.did. EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: US-P6PUB: EPC: JPC: DERWENT USPAT: USPAT	-	0	uk-1222969-\$.did.	USPAT;	2003/04/30
gb-1222969-\$.did. DERWENT USPAT; US-P6PUB; EPO; JPO; DERWENT US-P6PUB; EPO; JPO; D				US-PGPUB;	09:07
1 gb-122969-\$.did.				EPO; JPO;	
- 59 (204/\$.ccls. or 205/\$.ccls.) and bubble and (pressure near (module or modulating or pulse or pulsating or pulsed or pulsing or pulsed or varied or vari				DERWENT	
- 59 (204/\$.ccls. or 205/\$.ccls.) and bubble and (pressure near (module or modulating or pulse or pulsating or pulsed or pulsing or pulsed or varied or variable or cyclical)) - 8 (204/\$.ccls. or 205/\$.ccls.) and (bubble with (pressure near (module or modulating or pulsated or varied or variable or cyclical))) - 1012 (204/\$.ccls. or 205/\$.ccls.) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsed or pulsing or pulsated or varied or variable or cyclical))) - 102 (204/\$.ccls. or 205/\$.ccls.) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsed or pulsing or pulsated or varied or variable or cyclical))) - 21529 (204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board)) and bubble - 2051 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and bubble - 241 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) - 241 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) - 25 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsed or pulsated or varied or variable or cyclical))) - 26 (204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circu	_	1	gb-1222969-\$.did.	USPAT;	2003/04/30
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2051 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and bubble 241 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) 69 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) 69 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulating or pulse or pulsating or pulsating or pulsated or varied or variable or cyclical))) 5865894.pn. DERWENT US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT 10:20 US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO;					
- 2051 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and bubble - 241 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) - 69 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) - (204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsated or varied or varied or variable or cyclical))) - 2 5865894.pn. 2003/04/30 USPAT; 2003/04/30 USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; DERWENT			, , , , , , , , , , , , , , , , , , , ,		
wafer or microelectronic or (integrated adj circuit) or (circuit board))) and bubble 241 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) 49 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble or gas) same (pressure near (modulate or modulating or pulsed or varied or varied or variable or cyclical))) 5865894.pn. 2003/04/30 US-PGPUB; EPO; JPO; DERWENT	_	2051	((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or		2003/04/30
or (circuit board))) and bubble 241 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) 69 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsated or varied or variable or cyclical))) 2 5865894.pn. EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; DERWENT 10:20 USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO;			1 11	·	}
- 241 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) - 69 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulating or pulsated or varied or variable or cyclical))) - 2 7 8 8 6 5 8 9 4.pn. DERWENT USPAT; 2003/04/30 US-PGPUB; EPO; JPO; DERWENT 10:20 10:20 US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT 10:20 10:20 10:20 10:20 10:20 10:20 US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT 10:20 10:				· ·	
- 241 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) - 69 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsated or varied or variable or cyclical))) - 2 5865894.pn. 2003/04/30 USPAT; 2003/04/30 USPAT; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT			· · · · · · · · · · · · · · · · · · ·		
wafer or microelectronic or (integrated adj circuit) or (circuit board))) and (bubble with pressure) 69 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsated or varied or variable or cyclical))) 2 10:20 EPO; JPO; DERWENT US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO;	-	241	((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or		2003/04/30
or (circuit board))) and (bubble with pressure) 69 ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsated or varied or variable or cyclical))) 2 2 5865894.pn. EPO; JPO; DERWENT EPO; JPO; DERWENT US-PGPUB; EPO; JPO; USPAT; 2003/04/30 US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;			1 1		
- ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsated or varied or variable or cyclical))) 2 (204/\$.ccls. or 205/\$.ccls.) and (semiconductor or USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; USPAT; USPAT; USPAT; USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;					
- ((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsated or varied or variable or cyclical))) 2 (203/04/30 US-PGPUB; EPO; JPO; DERWENT US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;					
wafer or microelectronic or (integrated adj circuit) or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsed or pulsing or pulsated or varied or variable or cyclical))) 2 5865894.pn. US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO;	-	69	((204/\$.ccls. or 205/\$.ccls.) and (semiconductor or		2003/04/30
or (circuit board))) and ((bubble or gas) same (pressure near (modulate or modulation or modulating or pulse or pulsating or pulsated or varied or variable or cyclical))) 2 5865894.pn. EPO; JPO; DERWENT USPAT; USPAT; US-PGPUB; EPO; JPO;					
(pressure near (modulate or modulation or modulating or pulse or pulsating or pulsated or varied or variable or cyclical))) 2 5865894.pn. USPAT; 2003/04/30 US-PGPUB; 13:41 EPO; JPO;					
or pulse or pulsating or pulsing or pulsated or varied or variable or cyclical))) 2 5865894.pn. USPAT; 2003/04/30 US-PGPUB; 13:41 EPO; JPO;					
or varied or variable or cyclical))) 2 5865894.pn. USPAT; 2003/04/30 US-PGPUB; 13:41 EPO; JPO;					
- 2 5865894.pn. USPAT; 2003/04/30 US-PGPUB; 13:41 EPO; JPO;					
US-PGPUB; 13:41 EPO; JPO;	-	2		USPAT:	2003/04/30
EPO; JPO;			·		
]			
I DEKWENT !				DERWENT	

-	83136	204/\$.ccls. or 205/\$.ccls.	USPAT;	2003/04/30
			US-PGPUB;	13:41
			EPO; JPO;	
			DERWENT	
_	18	(204/\$.ccls. or 205/\$.ccls.) and (semiconductor) and	USPAT;	2003/04/30
		(bubbles with (sonic or ultrasonic or megasonic))	US-PGPUB;	13:45
			EPO; JPO;	
			DERWENT	
-	2	((204/\$.ccls. or 205/\$.ccls.) and (semiconductor) and	USPAT;	2003/04/30
		(bubbles with (sonic or ultrasonic or megasonic))) and	US-PGPUB;	13:45
		(hermetically or sealed)	EPO; JPO;	
			DERWENT	
-	1933	(204/198,212,232,242,273,275.1.ccls. 204/224r.ccls.	USPAT;	2003/04/30
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd	IŁUS-PGPUB;	14:07
		427/96,98,443.1.ccls.) and semiconductor	EPO; JPO;	
			DERWENT	
-	506	((204/198,212,232,242,273,275.1.ccls.	USPAT;	2003/04/30
		204/224r.ccls.	US-PGPUB;	14:07
	}	205/88,98,122,123,125,148,157,183,184,187,261,291.cd		
		427/96,98,443.1.ccls.) and semiconductor) and	DERWENT	
-	135	€((€20)46/11985 ,212,232,242,273,275.1.ccls.	USPAT;	2003/04/30
		204/224r.ccls.	US-PGPUB;	14:08
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd	l∉PO; JPO;	
		427/96,98,443.1.ccls.) and semiconductor) and	DERWENT	
		electroless) and ((copper adj (sulfate or sulphate))		
-	61	6(((2044)1916),2113),232,242,273,275.1.ccls.	USPAT;	2003/04/30
		204/224r.ccls.	US-PGPUB;	14:11
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd		
		427/96,98,443.1.ccls.) and semiconductor) and	DERWENT	
		electroless) and ((copper adj (sulfate or sulphate))		
-	18	6(((204619.16),2173)23621, (MA) 1276312765 (biodissol)	USPAT;	2003/04/30
		204/224r.ccls.	US-PGPUB;	14:12
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd		
]	427/96,98,443.1.ccls.) and semiconductor) and	DERWENT	
]	electroless) and ((copper adj (sulfate or sulphate))		
-	2	6(((20461986,2173)2362,(4426,2737356dticler trasnfer)	USPAT;	2003/04/30
		204/224r.ccis.	US-PGPUB;	14:12
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd		
		427/96,98,443.1.ccls.) and semiconductor) and	DERWENT	
		electroless) and ((copper adj (sulfate or sulphate))		

or "cuso.sub.4")) and hermetically

	T		T	
-	31	(=	USPAT;	2003/04/30
		or US-5433840-\$ or US-6294059-\$ or	US-PGPUB;	14:56
		US-5437777-\$ or US-6309524-\$ or US-5932077-\$	EPO; JPO;	
		or US-5522975-\$ or US-5415890-\$ or	DERWENT	
		US-6197181-\$ or US-4666735-\$ or US-6140234-\$		
		or US-6117784-\$ or US-4749449-\$ or		
		U5-4490220-\$ or U5-4303443-\$ or		
		US-6458251-\$).did. or (US-20020000372-\$ or		
		US-20020008034-\$ or US-20020005359-\$).did. or		
		(GB-2285174-\$ or US-5342806-\$).did. or		
		(JP-56158424-\$ or JP-05311496-\$ or		
		JP-07193214-\$ or JP-56161221-\$ or JP-03146698-\$		
		or JP-63026400-\$).did. or (JP-56158424-\$ or		
		GB-2285174-\$ or JP-63026400-\$ or		
		68-1222969-\$).did.		
	11		LICO 4 T	000000000000
-	"	((US-4163705-\$ or US-5849171-\$ or US-4430173-\$	USPAT;	2003/04/30
		or US-5433840-\$ or US-6294059-\$ or	US-PGPUB;	14:57
1		US-5437777-\$ or US-6309524-\$ or US-5932077-\$	EPO; JPO;	
	!	or US-5522975-\$ or US-5415890-\$ or	DERWENT	
1		US-6197181-\$ or US-4666735-\$ or US-6140234-\$		
		or US-6117784-\$ or US-4749449-\$ or		
		US-4490220-\$ or US-4303443-\$ or		
		US-6458251-\$).did. or (US-20020000372-\$ or		
		US-20020008034-\$ or US-20020005359-\$).did. or		
		(GB-2285174-\$ or US-5342806-\$).did. or		
		(JP-56158424-\$ or JP-05311496-\$ or		
		JP-07193214-\$ or JP-56161221-\$ or JP-03146698-\$		
		or JP-63026400-\$).did. or (JP-56158424-\$ or		
		GB-2285174-\$ or JP-63026400-\$ or		
		GB-1222969-\$).did.) and (waste or disposal or		
		dispose or disposed)		
_	4	((US-4163705-\$ or US-5849171-\$ or US-4430173-\$	USPAT:	2003/04/30
		or US-5433840-\$ or US-6294059-\$ or	US-PGPUB;	14:57
		US-5437777-\$ or US-6309524-\$ or US-5932077-\$	EPO; JPO;	11.07
		or US-5522975-\$ or US-5415890-\$ or	DERWENT	
		US-6197181-\$ or US-4666735-\$ or US-6140234-\$	O CIVICIVI	
		or US-6117784-\$ or US-4749449-\$ or		
		US-4490220-\$ or US-4303443-\$ or		
		US-6458251-\$).did. or (US-20020000372-\$ or		
		US-20020008034-\$ or US-20020005359-\$).did. or		!
		(GB-2285174-\$ or US-5342806-\$).did. or		
1		'		
1		(JP-56158424-\$ or JP-05311496-\$ or		
1	[JP-07193214-\$ or JP-56161221-\$ or JP-03146698-\$		
		or JP-63026400-\$).did. or (JP-56158424-\$ or		
		GB-2285174-\$ or JP-63026400-\$ or		
	4	GB-1222969-\$).did.) and (waste or disposal)		
-	10914	204/198,212,232,242,273,275.1.ccls. 204/224r.ccls.	USPAT,	2003/04/30
		205/88,98,122,123,125,148,157,183,184,187,261,291.c	I	14:59
		427/96,98,443.1.ccls.	EPO; JPO;	
			DERWENT	
-	294	(204/198,212,232,242,273,275.1.ccls. 204/224r.ccls.	USPAT;	2003/04/30
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd	IsUS-PGPUB;	15:00
		427/96,98,443.1.ccls.) and electroless and (waste or	EPO; JPO;	
		disposal)	DERWENT	

-	209	(204/198,212,232,242,273,275.1.ccls. 204/224r.ccls.	USPAT;	2003/04/30
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd	ISUS-PGPUB;	15:00
		427/96,98,443.1.ccls.) and (electroless with (solution	EPO; JPO;	
		or bath)) and (waste or disposal)	DERWENT	
_	76	(204/198,212,232,242,273,275.1.ccls. 204/224r.ccls.	USPAT;	2003/04/30
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd	IsUS-PGPUB;	15:00
		427/96,98,443.1.ccls.) and ((electroless with	EPO; JPO;	
		(solution or bath)) same (waste or disposal))	DERWENT	
_	38	(204/198,212,232,242,273,275.1.ccls. 204/224r.ccls.	USPAT;	2003/04/30
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd	ISUS-PGPUB;	15:02
		427/96,98,443.1.ccls.) and ((electroless with	EPO; JPO;	
		(solution or bath)) with (waste or disposal))	DERWENT	
_	45	(204/198,212,232,242,273,275.1.ccls. 204/224r.ccls.	USPAT;	2003/04/30
		205/88,98,122,123,125,148,157,183,184,187,261,291.cd		15:02
		427/96,98,443.1.ccls.) and ((electroless near2	EPO; JPO;	
		(solution or bath)) same (waste or disposal))	DERWENT	
_	60	205/\$.ccls. and damascene and (electroless and	USPAT;	2003/05/01
		(electroplating or electroplated or electrolytically or	US-PGPUB;	08:48
		electrochemically))	EPO; JPO;	
		• • • • • • • • • • • • • • • • • • • •	DERWENT	
-	26	205/\$.ccls. and damascene and ((barrier or seed)	USPAT;	2003/05/01
		with electroless) and ((electroplating or	US-PGPUB;	08:49
		electroplated or electrolytically or electrochemically)	EPO; JPO;	
		with (seed or barrier))	DERWENT	
_	18	(204/\$.ccls. or 205/\$.ccls.) and (electroless near2	USPAT;	2003/05/01
		(solution or bath) with (waste or disposal or dispose))	US-PGPUB;	10:12
			EPO; JPO;	
			DERWENT	
_	522	(204/\$.ccls. or 205/\$.ccls.) and (zinc with (plating or	USPAT;	2003/05/01
		electroplating)) and ((alkali or "naoh" or "koh") with	US-PGPUB;	12:51
		((ammonium or tetramethylammonium) adj hydroxide)	EPO; JPO;	
		or alkaline)	DERWENT	
-	128	(204/\$.ccls. or 205/\$.ccls.) and (zinc with (plating or	USPAT;	2003/05/01
		electroplating)) and (((alkali or "naoh" or "koh") with	US-PGPUB;	12:52
		((ammonium or tetramethylammonium) adj hydroxide)	EPO; JPO;	
		or alkaline) with "ph")	DERWENT	
-	128	(204/\$.ccls. or 205/\$.ccls.) and (zinc with (plating or	USPAT;	2003/05/01
		electroplating)) and (((alkali! or "naoh" or "koh") with	US-PGPUB;	12:53
		((ammonium or tetramethylammonium) adj hydroxide)	EPO; JPO;	
		or alkaline) with "ph")	DERWENT	
-	35	(204/\$.ccls. or 205/\$.ccls.) and (zinc with (plating or	USPAT;	2003/05/01
		electroplating)) and (((alkali! or "naoh" or "koh") with	U5-PGPUB;	12:53
]	(((ammonium or tetramethylammonium) adj	EPO; JPO;	
		hydroxide) or alkaline)) with "ph")	DERWENT	